

HN62408 Series — Preliminary

524288-Word × 16-Bit/1048576-Word × 8-Bit CMOS Mask Programmable ROM

HN62408 Series is a 8-Mbit CMOS mask-programable ROM organized either as 524288-word x 16-Bit or as 1048576-Word x 8-Bit. It can be operated with a battery because of low power consumption. The large capacity of 8M bits is optimum for a kanji character generator.

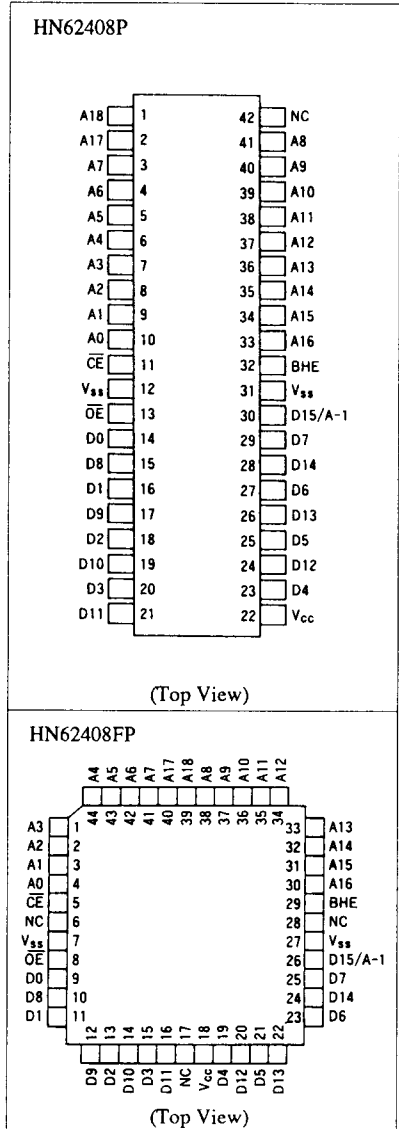
Features

- Single 5 V
- Wired OR is permitted for the output in three states
- TTL compatible
- Address access time: 200 ns (max)
- Low power: Active 100 mW (typ)
Standby 5 μ W (typ)
- Byte-Wide or Word-Wide Data Organization (switched by BHE terminal)

Ordering Information

Type No.	Address Access Time	Package
HN62408P	200 ns	600 mil 42-pin plastic DIP
HN62408FP	200 ns	44-pin plastic QFP

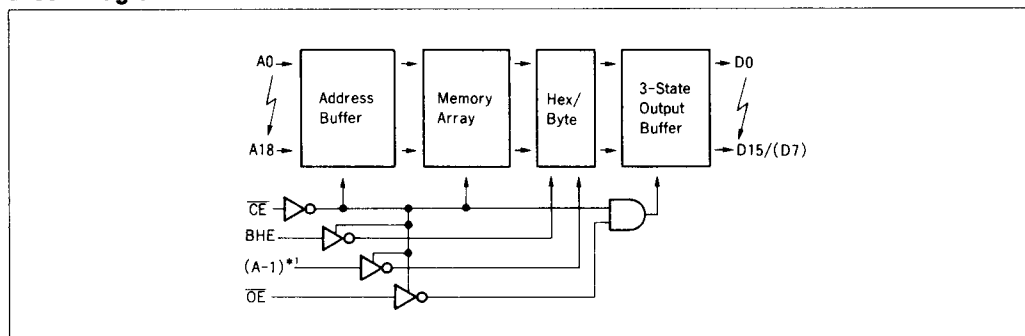
Pin Arrangement



Note: The specifications of this device are subject to change without notice.
Please contact your nearest Hitachi's Sale Dept. regarding specifications.



Block Diagram



BHE = V_{IH} : 16 bits (D15–D0)

BHE = V_{IL} : 8 bits (D7–D0)

*1: A-1 is least significant address input, and D14–D8 are of high impedance.

Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Power supply voltage*1	V_{CC}	-0.3 to +7.0	V
Terminal voltage*1	V_T	-0.3 to $V_{CC} + 0.3$	V
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	-55 to +125	°C
Bias temperature	T_{bias}	-20 to +85	°C

Note: *1. With respect to V_{SS} .

Recommended Operating Conditions ($V_{SS} = 0$ V, $T_a = 0$ to +70°C)

Item	Symbol	Min	Typ	Max	Unit
Power supply voltage	V_{CC}	4.5	5.0	5.5	V
Input voltage	V_{IH}	2.2	—	$V_{CC} + 0.3$	V
	V_{IL}	-0.3	—	0.8	V

DC Characteristics ($V_{CC} = 5$ V \pm 10%, $V_{SS} = 0$ V, $T_a = 0$ to +70°C)

Item	Symbol	Min	Max	Unit	Test Conditions	
Power supply current	Active	I_{CC}	—	50	mA	$V_{CC} = 5.5$ V, $I_{DOUT} = 0$ mA, $t_{rc} = \text{Min}$
	Standby	I_{SB}	—	30	μ A	$V_{CC} = 5.5$ V, $CE \geq V_{CC} - 0.2$ V
Input leak current	$ I_{LI} $	—	10	μ A	$V_{IN} = 0$ to V_{CC}	
Output leak current	$ I_{LO} $	—	10	μ A	$CE = 2.2$ V, $V_{OUT} = 0$ to V_{CC}	
Output voltage	V_{OH}	2.4	—	V	$I_{OH} = -205$ μ A	
	V_{OL}	—	0.4	V	$I_{OL} = 1.6$ mA	



Capacitance ($V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $T_a = 25^\circ\text{C}$, $V_{in} = 0\text{ V}$, $f = 1\text{ MHz}$)

Item	Symbol	Min	Max	Unit
Input capacitance*1	Cin	—	15	pF
Output capacitance*1	Cout	—	15	pF

Note: *1. This parameter is sampled and not 100% tested.

AC Operating Characteristics ($V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $T_a = 0\text{ to }+70^\circ\text{C}$)

Test Conditions

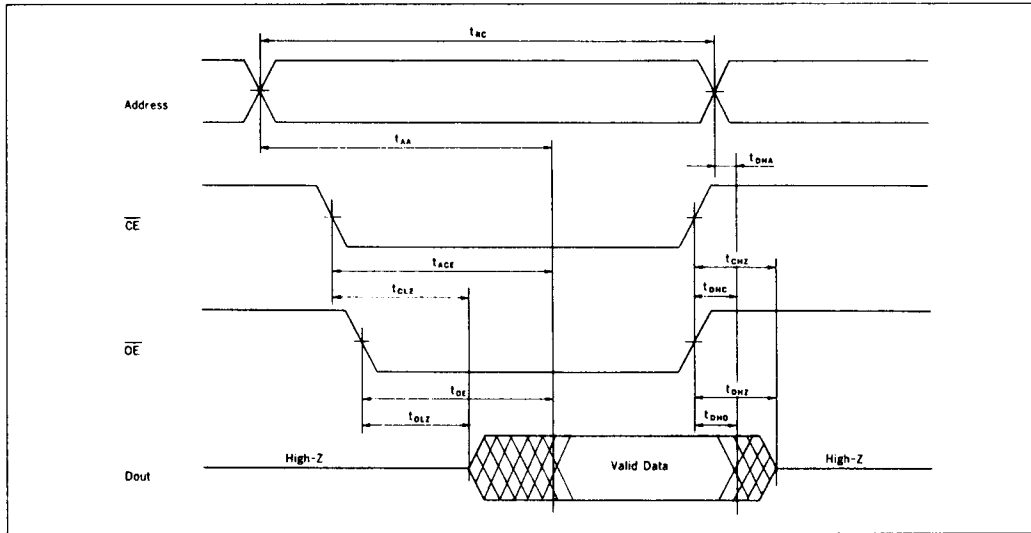
Input pulse level: 0.8 to 2.4 V Output load: 1 TTL gate + $C_L = 100\text{ pF}$
 I/O timing reference level: 1.5 V (including jig capacitance)
 Input rise/fall time: 10 ns

Item	Symbol	Min	Max	Unit
Cycle time	TRC	200	—	ns
Address access time	tAA	—	200	ns
CE access time	tACE	—	200	ns
OE access time	tOE	—	100	ns
BHE access time	tBHE	—	200	ns
Output Hold Time from Address Change	tDHA	0	—	ns
Output Hold Time from CE	tDHC	0	—	ns
Output Hold Time from OE	tDHO	0	—	ns
Output Hold Time from BHE	tDHB	0	—	ns
CE to Output in High Z	tCHZ*1	—	70	ns
OE to Output in High Z	tOHZ*1	—	70	ns
BHE to Output in High Z	tBHZ*1	—	70	ns
CE to Output in Low Z	tCLZ	10	—	ns
OE to Output in Low Z	tOLZ	10	—	ns
BHE to Output in Low Z	tBLZ	10	—	ns

Note: *1 tCHZ, tOHZ, and tBHZ define the time at which the output goes to the high impedance state and is not referenced to output voltage level.



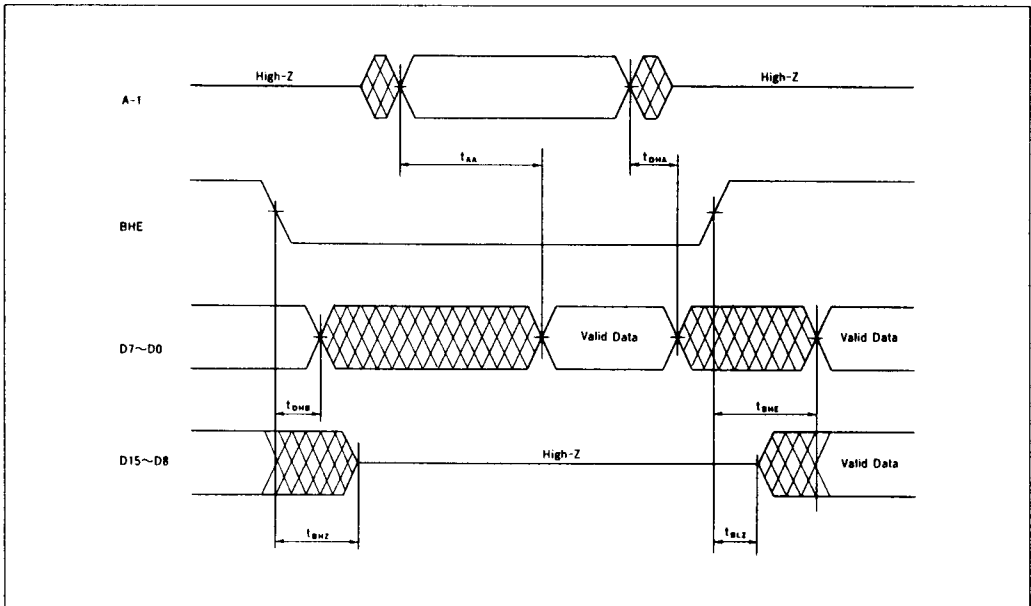
Timing Waveform
Word Mode (BHE = "V_{IH}") or Byte Mode (BHE = "V_{IL}")



- Notes:
- 1. tDHA, tDHC, tDHO; Determined by whichever is faster.
 - 2. tAA, tACE, tOE; Determined by whichever is slower.
 - 3. tCLZ, tOLZ; Determined by whichever is slower.



Switching between Word Mode and Byte Mode



- Notes:
1. \overline{CE} , \overline{OE} are of selected status. A18~A0 are fixed.
 2. D15/A-1 terminal is of output state when BHE = V_{IH}, CE and OE are of selected state. At this time, an input signal that is of the inverse phase to the output should not be impressed.